

# ZXMP3A16N8

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## 30V P-CHANNEL ENHANCEMENT MODE MOSFET

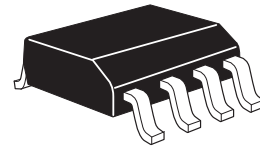
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### SUMMARY

$V_{(BR)DSS} = -30V$ ;  $R_{DS(ON)} = 0.040\Omega$ ;  $I_D = -6.7A$

### DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



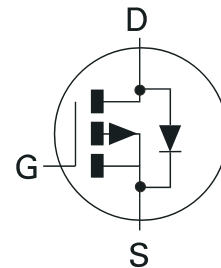
SO8

### FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

### APPLICATIONS

- Disconnect switches
- Motor control



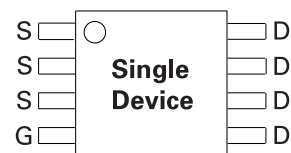
### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A16N8TA	7"	12mm	500 units
ZXMP3A16N8TC	13"	12mm	2500 units

### DEVICE MARKING

- ZXMP  
3A16

### PINOUT



Top View

# ZXMP3A16N8

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $V_{GS}=-10V; T_A=25^\circ C$ (b) $V_{GS}=-10V; T_A=70^\circ C$ (b) $V_{GS}=-10V; T_A=25^\circ C$ (a)	$I_D$	-6.7 -5.4 -5.6	A
Pulsed Drain Current (c)	$I_{DM}$	-26	A
Continuous Source Current (Body Diode) (b)	$I_S$	-3.2	A
Pulsed Source Current (Body Diode) (c)	$I_{SM}$	-26	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	$P_D$	1.9 15.2	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	$P_D$	2.8 22.4	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	65	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	45	$^\circ C/W$

### NOTES

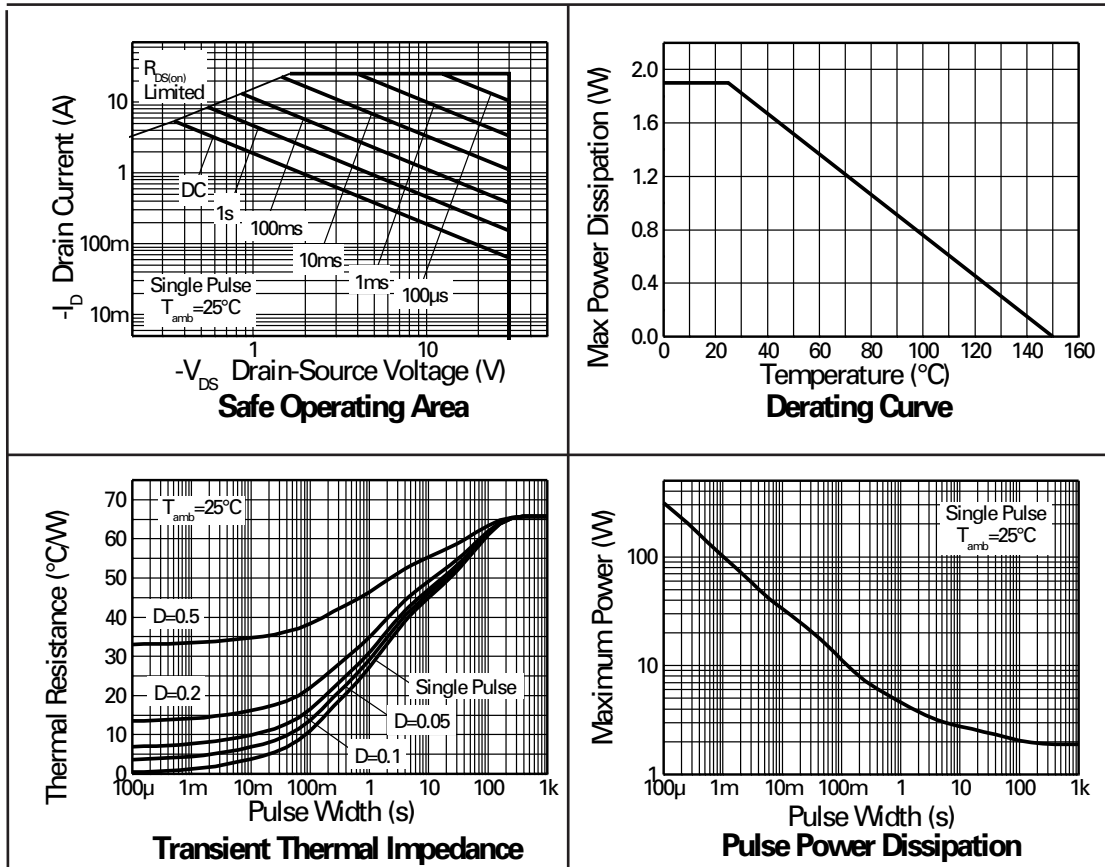
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at  $t \leq 5$  secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB,  $D = 0.05$ , pulse width  $10 \mu s$  - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

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## CHARACTERISTICS



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## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

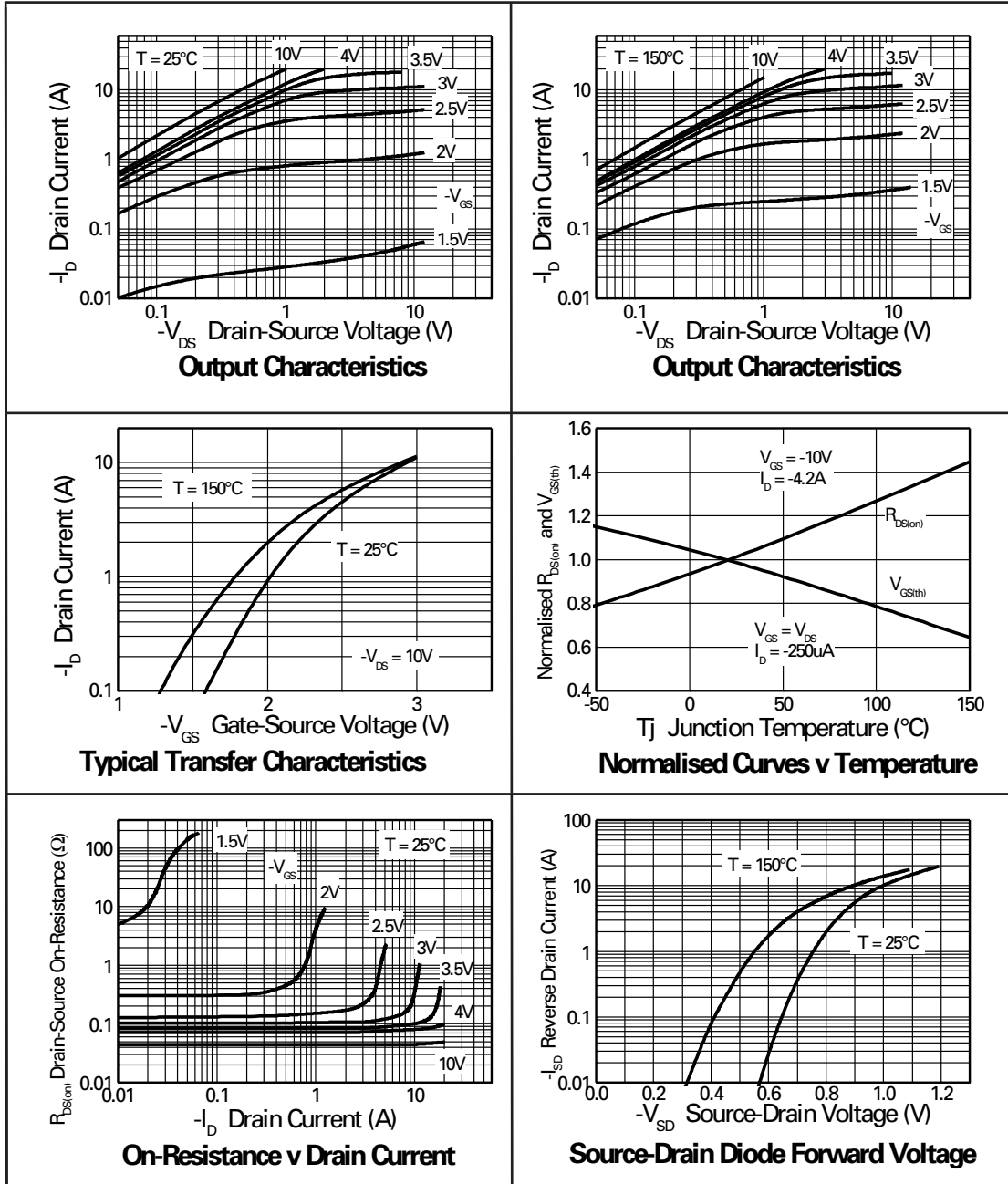
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$			-1.0	$\mu\text{A}$	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.040 0.070	$\Omega$ $\Omega$	$V_{GS} = -10\text{V}, I_D = -4.2\text{A}$ $V_{GS} = -4.5\text{V}, I_D = -3.4\text{A}$
Forward Transconductance (1)(3)	$g_{fs}$		9.2		S	$V_{DS} = -15\text{V}, I_D = -4.2\text{A}$
<b>DYNAMIC (3)</b>						
Input Capacitance	$C_{iss}$		1022		pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$		267		pF	
Reverse Transfer Capacitance	$C_{rss}$		229		pF	
<b>SWITCHING(2) (3)</b>						
Turn-On Delay Time	$t_{d(on)}$		3.8		ns	$V_{DD} = -15\text{V}, I_D = -1\text{A}$ $R_G = 6.0\Omega, V_{GS} = -10\text{V}$
Rise Time	$t_r$		6.5		ns	
Turn-Off Delay Time	$t_{d(off)}$		37.1		ns	
Fall Time	$t_f$		21.4		ns	
Gate Charge	$Q_g$		17.2		nC	$V_{DS} = -15\text{V}, V_{GS} = -5\text{V},$ $I_D = -4.2\text{A}$
Total Gate Charge	$Q_g$		29.6		nC	$V_{DS} = -15\text{V}, V_{GS} = -10\text{V},$ $I_D = -4.2\text{A}$
Gate-Source Charge	$Q_{gs}$		2.8		nC	
Gate-Drain Charge	$Q_{gd}$		8.6		nC	
<b>SOURCE-DRAIN DIODE</b>						
Diode Forward Voltage (1)	$V_{SD}$		-0.85	-0.95	V	$T_J = 25^{\circ}\text{C}, I_S = -3.6\text{A},$ $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	$t_{rr}$		21.7		ns	$T_J = 25^{\circ}\text{C}, I_F = -2\text{A},$ $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	$Q_{rr}$		16.1		nC	

### NOTES

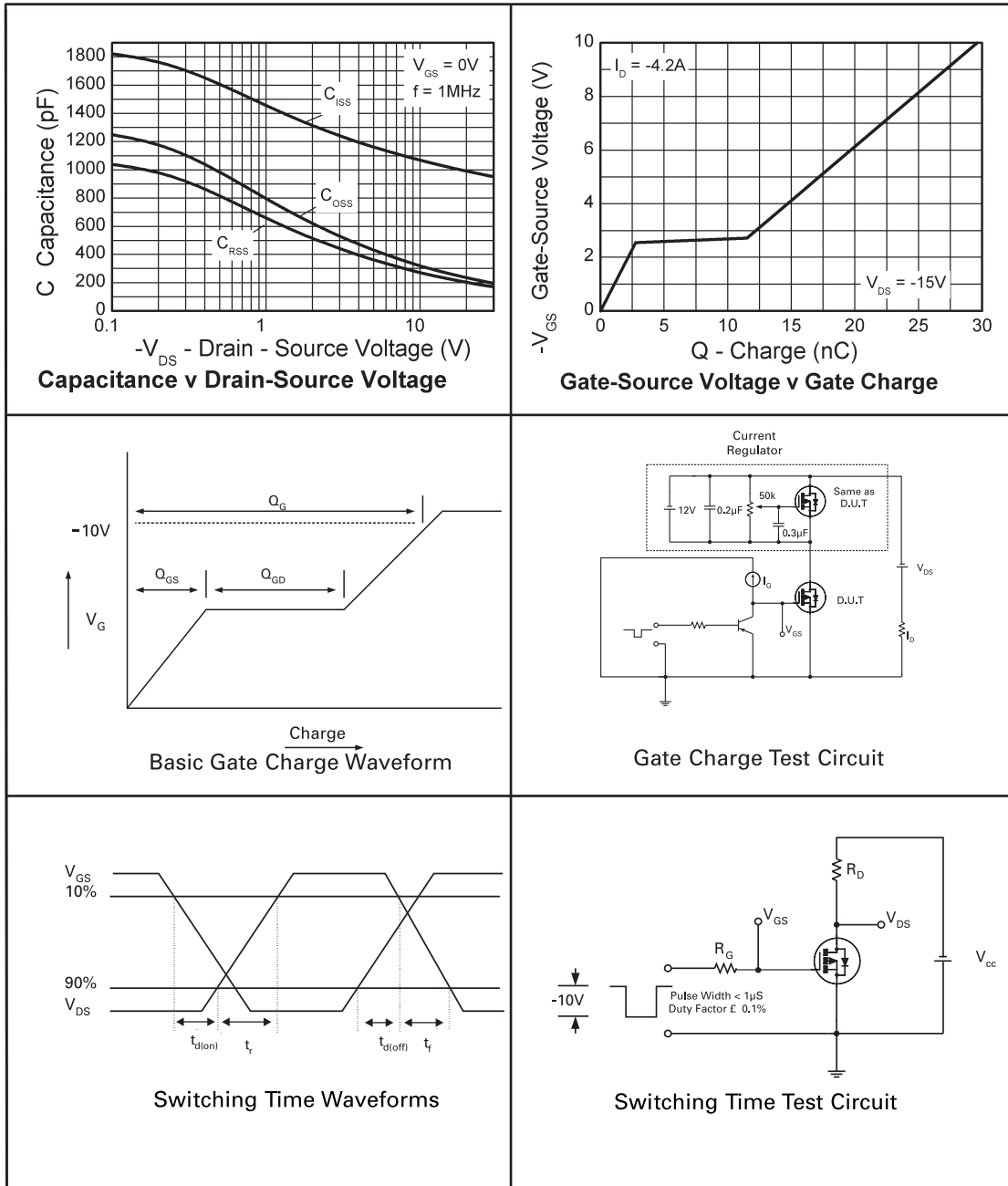
- (1) Measured under pulsed conditions. Width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .  
 (2) Switching characteristics are independent of operating junction temperature.  
 (3) For design aid only, not subject to production testing.

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## CHARACTERISTICS



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"Not recommended for new designs"Device is still in production to support existing designs and production

"Obsolete"Production has been discontinued

Datasheet status key:

"Draft version" This term denotes a very early datasheet version and contains highly provisional information, which may change in any manner without notice.

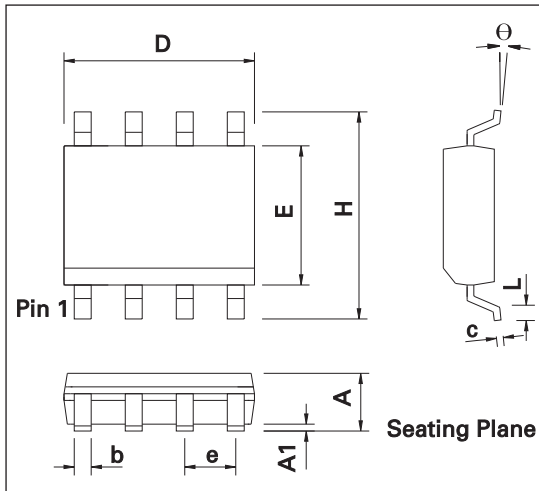
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## PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES  
APPROX IN MILLIMETERS

## PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.35	1.75	0.053	0.069	e	1.27 BSC		0.050 BSC	
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	c	0.19	0.25	0.008	0.010
H	5.80	6.20	0.228	0.244	θ	0°	8°	0°	8°
E	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-

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